## Package to Board Linkage capacitance – Cp Extraction/Simulation Follow-up

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IEEE802.3ck Telephonic Plenary meeting Date: March 2021

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#### Package to board linkage "Ball area" capacitance

#### Reminder – Recap / Main points:

• Ad hoc slides (integrated from slide 8 and on as a reminder) claimed:

Extraction/Simulation follow-up

- The appropriate manner to evaluate Cp is by looking at its reflective effect, rather than calculate the capacitance of the mechanical structure –
- A short background recap of the methodology originally used to corelate the package model effect and with it the ball discontinuity effect will also be presented for further emphasis
- The impedance drop due to 87fF Cp is reasonable, while driving a whole package by a 7.5psec t<sub>r</sub> TDR – Will be further emphasized by correlating a ball extraction (with as little a package as possible) by itself

#### Extraction/Simulation follow-up Ball Fringing Capacitance Effect

 What would be the effective capacitive reflective effect of a ball (after assembly) (in Green) with the exact same size void (No overlap) formed on the GND (blue) layer 30µ above it?



## Package to board linkage "Ball area" capacitance Extraction/Simulation follow-up

#### Follow-up - TDR of a ball by itself

- Effective capacitance of a ball while utilizing methodologies to lower ball area capacitance  $\approx$  80fF prior to manufacturing tolerances -Correlates to 802.3ck Cp
- Fringing effect of a ball with the exact same diameter void placed above it ≈ 125fF - Correlates to Cp of 802.3bj



#### Extraction / Simulation Follow-up Summary

- Extraction/Simulation follow-up The fringing capacitance by itself correlates to 802.3bj Cp value
- Some valid packaging applications may require mechanical implications on ball area which are likely to be translated to higher capacitance
- Methods were used to lower ball-area capacitance and the discontinuity of the resulting structure was correlated to 80fF (before applying manufacturing tolerance)
- We have verified that former values of Cp indeed corelate to as basic as possible models
- →Cp value of 87fF is reasonable and should not be changed

### Background – Package Synthesis Model Process Overview



- 1. Start from measured or simulated multiport s-parameter not including the die load
  - One set of ports will be the die connect to the package referenced to die reference plane
  - The other side will be the BGA (if applicable) ball with port referenced to the PCB or carrier's reference plane
  - Must have sufficient bandwidth, causality, passivity, and stability for time domain analysis at the prescribed baud rate.
- 2. Identify a die circuit model to use for synthesis.
- 3. Identify then extract a 4 port victim set of s-parameters
- 4. Acquire IL and RL vs Frequency plots, Pulse response (PR) plots, TDR plots PTDR plots

- 5. Estimate an target for the synthesized circuit.
  - TDR plots
  - This step requires some engineering experience a judgement
- 6. Identify transmission line segments and make estimates for loss, delay and Z<sub>0</sub>.
- 7. Iterate through comparison between the synthesis models and the original s-parameter model
  - Adjust circuit and T-line parameter to get a acceptable overlays of the pulse response, TDR, PTDR, IL and RL
- 8. Finally use both models to do COM simulations
  - If results are close enough, say 0.05 dB you are done

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#### Thank You!

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# January 2021 Ad Hoc Slides here-on

- 1. Package imperfections and inclusion in the reference model
- 2. Package to board linkage "Ball area" capacitance
- 3. Cp TDR Results
- 4. Summary

#### Package imperfections and inclusion in the reference model

- Loss Included, may fall short of max, or long of min loss
- Length Two reference lengths may fall short of max, or long of min length, may not introduce worst re-reflections given specific interconnects
- Bump area discontinuity model included to represent silicon "T-Coil" and bump discontinuity
- Trace + PTH impedances Models are included to represent impedances of the trace and the PTH with delay relative length – Manufacturing tolerances are not represented and package vias were optimized to bring best COM result, one PTH location close to the ball
- Package cross lane Far-end/Near-end Crosstalk Not included
- Ball-area discontinuity Next Slide

#### Package to board linkage "Ball area" capacitance

- Device package including 100Gbps lanes vary in size and type
  - Various types and sizes can have different ball-area characteristic impedance discontinuity.
    - Implementation requirements vary, mechanical requirements vary, manufacturing tolerance vary
- Package to board linkage capacitance is used to emulate reference package ball area discontinuity and is called Cp
  - A more complicated model was avoided thanks to ball-area dimensions relative to wavelength. For better accuracy can increase complexity – no need
  - Correlation to extractions (No board pad coax port on ball) was provided in <u>https://www.ieee802.org/3/ck/public/19\_01/benartsi\_3ck\_01\_0119.pdf</u>
- The usage of Cp is in the time domain in COM and TP0v simulations
  - Discontinuity in time domain is best estimated by time domain reflectometry

## Cp TDR using COM rise-time (7.5psec)



## Summary

- The reference package model does not incorporate multiple manufacturing related and design related items 3dB COM
- Loss and reflections are a major contributor to the reference package model imperfections
- The reference package model is used for simulation in the timedomain, thus one should look at its effect in time domain reflectometry
- It was demonstrated that 87fF introduce a reasonable discontinuity not best case, for sure not worst case

# Thank you!